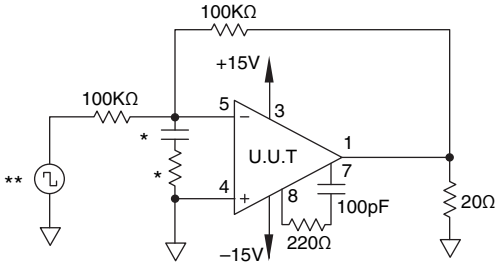
SG	PARAMETER	SYMBOL	TEMP.	POWER	TEST CONDITIONS	MIN	MAX	UNITS
1	Quiescent Current	I_Q	25°C	±35V	V_{IN} = 0, A_V = 100		85	mA
1	Input Offset Voltage	V_{OS}	25°C	±35V	V_{IN} = 0, A_V = 100		3	mV
1	Input Offset Voltage	V_{OS}	25°C	±12V	V_{IN} = 0, A_V = 100		5.3	mV
1	Input Offset Voltage	V_{OS}	25°C	±40V	V_{IN} = 0, A_V = 100		3.5	mV
1	Input Bias Current, +IN	$+I_B$	25°C	±35V	V_{IN} = 0		100	pA
1	Inout Bias Current, –IN	$–I_B$	25°C	±35V	V_{IN} = 0		100	pA
1	Input Offset Current	I_{OS}	25°C	±35V	V_{IN} = 0		50	pA
3	Quiescent Current	I_Q	–55°C	±35V	V_{IN} = 0, A_V = 100		165	mA
3	Input Offset Voltage	V_{OS}	–55°C	±35V	V_{IN} = 0, A_V = 100		5.4	mV
3	Input Offset Voltage	V_{OS}	–55°C	±12V	V_{IN} = 0, A_V = 100		7.7	mV
3	Input Offset Voltage	V_{OS}	–55°C	±40V	V_{IN} = 0, A_V = 100		5.9	mV
3	Input Bias Current, +IN	$+I_B$	–55°C	±35V	V_{IN} = 0		100	pA
3	Input BiasCurrent, –IN	$–I_B$	–55°C	±35V	V_{IN} = 0		100	pA
3	Input Offset Current	I_{OS}	–55°C	±35V	V_{IN} = 0		50	pA
2	Quiescent Current	I_Q	125°C	±35V	V_{IN} = 0, A_V = 100		140	mA
2	Input Offset Voltage	V_{OS}	125°C	±35V	V_{IN} = 0, A_V = 100		6	mV
2	Input Offset Voltage	V_{OS}	125°C	±12V	V_{IN} = 0, A_V = 100		8.3	mV
2	Input Offset Voltage	V_{OS}	125°C	±40V	V_{IN} = 0, A_V = 100		6.5	mV
2	Input Bias Current, +IN	$+I_B$	125°C	±35V	V_{IN} = 0		10	nA
2	Input Bias Current, –IN	$–I_B$	125°C	±35V	V_{IN} = 0		10	nA
2	Input Offset Current	I_{OS}	125°C	±35V	V_{IN} = 0		10	nA
4	Output Voltage, I_O = 3A	V_O	25°C	±21.3V	R_L = 3.75Ω	11.3		V
4	Output Voltage, I_O = 66mA	V_O	25°C	±40V	R_L = 500Ω	33		V
4	Output Voltage, I_O = 2A	V_O	25°C	± 38V	R_L = 15Ω	30		V
4	Current Limits	I_{CL}	25°C	±32.2V	R_L = 3.75Ω	3.4	6	A
4	Stability/Noise	E_N	25°C	±35V	R_L = 500Ω, A_V = 1, C_L = 1.5nF		1	mV
4	Slew Rate	SR	25°C	±35V	R_L = 500Ω	25	500	V/µs
4	Open Loop Gain	A_{OL}	25°C	±35V	R_L = 500Ω, F = 10Hz	80		dB
4	Common Mode Rejection	CMR	25°C	±34.5V	R_L = 500Ω, F = DC, V_{CM} = ±22.5V	64		dB
6	Output Voltage, I_O = 3A	V_O	–55°C	±21.3V	R_L = 3.75Ω	11.3		V
6	Output Voltage, I_O = 66mA	V_O	–55°C	±40V	R_L = 500Ω	33		V
6	Output Voltage, I_O = 2A	V_O	–55°C	±38V	R_L = 15Ω	30		V
6	Stability/Noise	E_N	–55°C	±35V	R_L = 500Ω, A_V = 1, C_L = 1.5nF		1	mV
6	Slew Rate	SR	–55°C	±35V	R_L = 500Ω	25	500	V/µs
6	Open Loop Gain	A_{OL}	–55°C	±35V	R_L = 500Ω, F = 10Hz	80		dB
6	Common Mode Rejection	CMR	–55°C	±34.5V	R_L = 500Ω, F = DC, V_{CM} = ±22.5V	64		dB
5	Output Voltage, I_O = 66mA	V_O	125°C	±40V	R_L = 500Ω	33		V
5	Output Voltage, I_O = 1A	V_O	125°C	±23.5V	R_L = 15Ω	15		V
5	Stability/Noise	E_N	125°C	±35V	R_L = 500Ω, A_V = 1, C_L = 1.5nF		1	mV
5	Slew Rate	SR	125°C	±35V	R_L = 500Ω,	20	500	V/µs
5	Open Loop Gain	A_{OL}	125°C	±35V	R_L = 500Ω, F = 10Hz	80		dB
5	Common Mode Rejection	CMR	125°C	±34.5V	R_L = 500Ω, F = DC, V_{CM} = ±22.5V	64		dB

BURN IN CIRCUIT



* These components are used to stabilize device due to poor high frequency characteristics of burn in board.

** Input signals are calculated to result in internal power dissipation of approximately 2.1W at case temperature = 125°C.

This data sheet has been carefully checked and is believed to be reliable, however, no responsibility is assumed for possible inaccuracies or omissions. All specifications are subject to change without notice.